

Silicon PNP Power Transistors

D45H8

DESCRIPTION

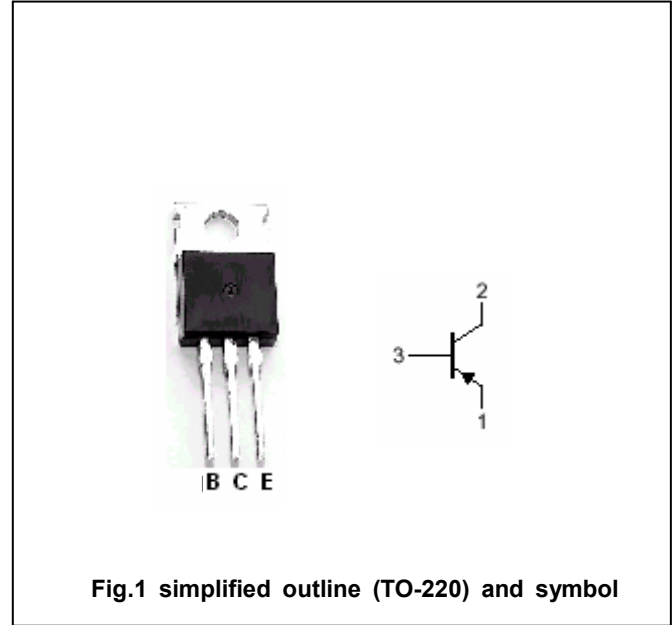
- With TO-220C package
- Fast switching speeds
- Low collector saturation voltage

APPLICATIONS

- For general purpose power amplifications and switching regulators, converters and power amplifiers applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings (Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-60	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-10	A
I _{CM}	Collector current-Peak		-20	A
P _D	Total power dissipation	T _C =25°C	50	W
		T _a =25°C	1.67	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance from junction to case	2.5	°C/W

Silicon PNP Power Transistors

D45H8

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-10mA I _B =0,	-60			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-8A ;I _B =-0.4A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-8A ;I _B =-0.8A			-1.5	V
I _{CES}	Collector cut-off current	V _{CE} =-80V; V _{BE} =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-0.1	mA
h _{FE-1}	DC current gain	I _C =-2A ; V _{CE} =-1V	60			
h _{FE-2}	DC current gain	I _C =-4A ; V _{CE} =-1V	40			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V		40		MHz
C _{cb}	Collector capacitance	f=1MHz ; V _{CB} =-10V		230		pF

Switching times

t _{on}	Turn-on time	I _C =-5A I _{B1} =- I _{B2} =-0.5A		135		ns
t _s	Storage time			0.5		μs
t _f	Fall time			0.10		μs

Silicon PNP Power Transistors

D45H8

PACKAGE OUTLINE

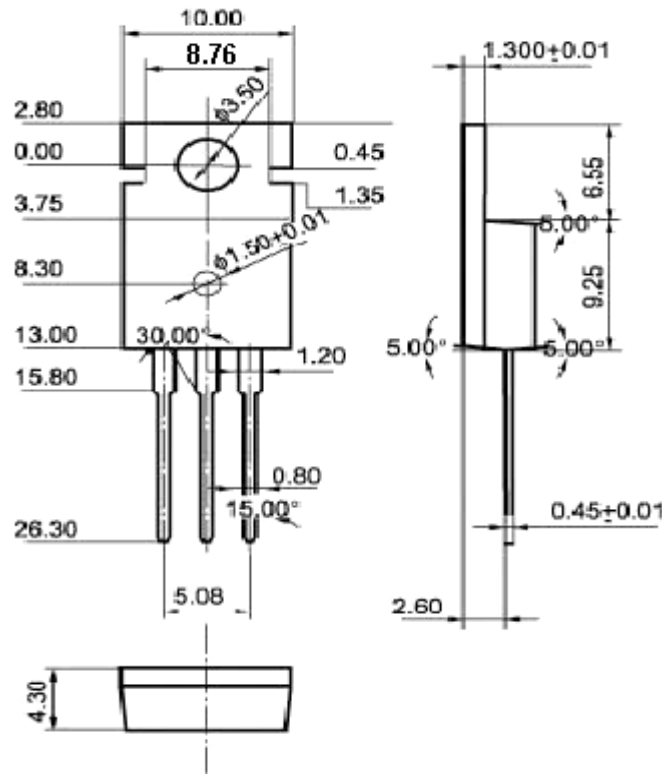


Fig.2 Outline dimensions (unindicated tolerance: ±0.10mm)